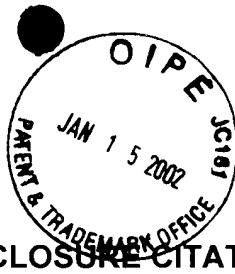


Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

Sheet 1 of 1.

Docket # SMJ-003

In re application of: James J. Mezey, Sr.

Serial Number: 09/900,594

Filed: 07/07/2001

GAU: 2812

## U.S. PATENT DOCUMENTS

Examiner Initials	Cite	Patent No.	Issue Date	Name	Class	Subclass	Filing Date
E	CA	5,440,101	08/08/95	Cox et al.	219	388	04/19/93
E	CB	5,854,468	12/29/98	Muka	219	443	01/25/96
E	CC	5,911,896	06/15/99	Holden et al.	219	390	06/25/97
E	CD	6,111,225	08/29/00	Ohkase et al.	219	390	02/21/97
E	CE	6,139,641	10/31/00	Inokuchi et al.	118	724	06/24/97
E	CF	6,214,116	04/10/01	Shin	118	640	01/18/99

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite	Foreign Patent Document	Publish Date	Name	Pages	T
E	DA	EP 0874387 A1	10/28/98	Jorg et al.		
E	DB	JP 10-83966	03/31/98			
E	DC	JP 11-312650	11/09/99			
E	DD	JP 56-32400	04/01/81			
E	DE	JP 60-112694	06/19/85			
E	DF	WO 97/31389	08/28/97			
E	DG	WO 00/12945	03/09/00	Griffiths et al.		

Examiner Signature

Date Considered

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form in next communication to the applicant.


**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Docket # **SMJ-003**  
 In re application of: **James J. Mezey, Sr.**  
 Serial Number: **09/900,594**  
 Filed: **07/07/2001**  
 GAU: **2812**

**OTHER DOCUMENTS AND NON-PATENT LITERATURE DOCUMENTS**

Initials	Cite		T
	EA	International Search Report for PCT Application PCT/US01/40511, date of mailing 10/02/2001	
	EB	Patent Abstracts of Japan, Publication No. 10083966, Publication Date 03/31/98, Application Date 06/23/97, Application No. 09181745, title "Substrate Processing Device," inventor Ikeda.	
	EC	Patent Abstracts of Japan, Publication No. 11312650, Publication Date 11/09/99, Application Date 01/18/99, Application No. 11009728, title "Horizontal Reaction Furnace for Manufacturing Compound Semiconductor," inventor Shin.	
	ED	Patent Abstracts of Japan, Publication No. 56032400, Publication Date 04/01/81, Application Date 08/16/79, Application No. 54103580, title "Vapor Phase Growing Method For Gallium Phosphide Layer," inventor Hisatomi	
	EE	Patent Abstracts of Japan, Publication No. 60112694, Publication Date 06/19/85, Application Date 11/21/83, Application No. 58218929, title "Gas Phase Growth Method of Compound Semiconductor," inventor Hase.	

Examiner Signature

Date Considered

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form in next communication to the applicant.

RECEIVED  
JAN 28 2002  
TC 1700